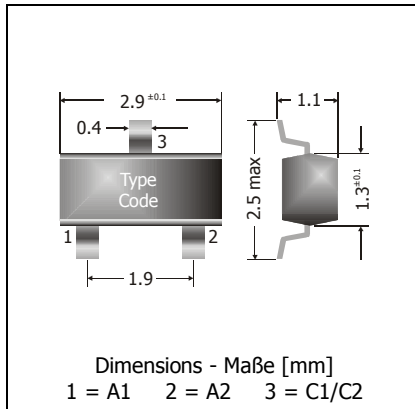


BAV23CC
Surface Mount Small Signal Dual-Diodes
Kleinsignal-Doppel-Dioden für die Oberflächenmontage

Version 2010-06-14



Power dissipation – Verlustleistung

350 mW

 Repetitive peak reverse voltage
 Periodische Spitzensperrspannung

250 V

 Plastic case
 Kunststoffgehäuse

 SOT-23
 (TO-236)

Weight approx. – Gewicht ca.

0.01 g

 Plastic material has UL classification 94V-0
 Gehäusematerial UL94V-0 klassifiziert

 Standard packaging taped and reeled
 Standard Lieferform gegurtet auf Rolle
**Maximum ratings (T_A = 25°C)****Grenzwerte (T_A = 25°C)**

per diode / pro Diode		BAV23CC	
Power dissipation – Verlustleistung ¹⁾		P _{tot}	350 mW ²⁾
Max. average forward current (dc) Dauergrenzstrom		I _{FAV}	400 mA ²⁾
Repetitive peak forward current Periodischer Spitzenstrom		I _{FRM}	625 mA ²⁾
Non repetitive peak forward surge current Stoßstrom-Grenzwert	t _p ≤ 10 ms	I _{FSM}	1.7 A
	t _p ≤ 100 µs	I _{FSM}	3 A
	t _p ≤ 1 µs	I _{FSM}	9 A
Repetitive peak reverse voltage Periodische Spitzensperrspannung		V _{RRM}	250 V
Junction temperature – Sperrschichttemperatur		T _j	-55...+150°C
Storage temperature – Lagerungstemperatur		T _S	-55...+150°C

Characteristics (T_j = 25°C)**Kennwerte (T_j = 25°C)**

Forward voltage Durchlass-Spannung	I _F = 100 mA		V _F	< 1 V
	I _F = 200 mA		V _F	< 1.25 V
Leakage current ³⁾ Sperrstrom	T _j = 25°C	V _R = 200 V	I _R	< 100 nA
	T _j = 150°C	V _R = 200 V	I _R	< 100 µA

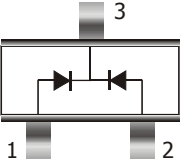
1 Total power dissipation of both diodes – Summe der Verlustleistungen beider Dioden

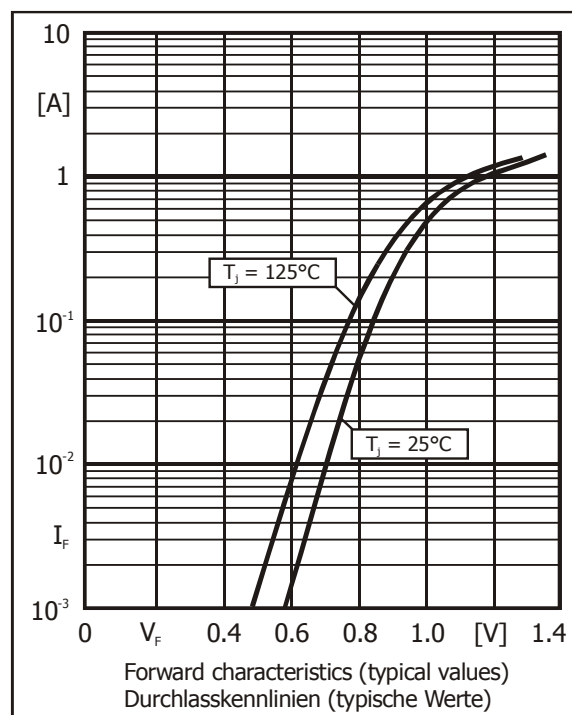
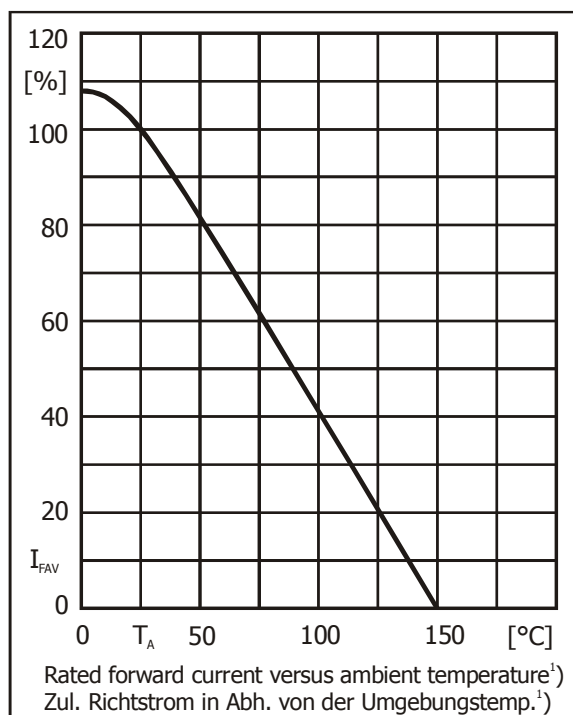
2 Mounted on P.C. board with 3 mm² copper pad at each terminal
 Montage auf Leiterplatte mit 3 mm² Kupferbelag (Lötpad) an jedem Anschluss

3 Tested with pulses t_p = 300 µs, duty cycle ≤ 2% – Gemessen mit Impulsen t_p = 300 µs, Schaltverhältnis ≤ 2%

Characteristics ($T_j = 25^\circ\text{C}$)
Kennwerte ($T_j = 25^\circ\text{C}$)

Max. junction capacitance – Max. Sperrschichtkapazität $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_T	5 pF
Reverse recovery time – Sperrverzug $I_F = 30\text{ mA}$ über/through $I_R = 30\text{ mA}$ bis/to $I_R = 3\text{ mA}$, $R_L = 100\ \Omega$	t_{rr}	< 50 ns
Thermal resistance junction to ambient air Wärmewiderstand Sperrschicht – umgebende Luft	R_{thA}	< 357 K/W ¹⁾

Pinning – Anschlussbelegung		Marking – Stempelung
		BAV23CC = PZ
Double diode, common cathode Doppeldiode, gemeinsame Kathode $1 = A1$ $2 = A2$ $3 = C1/C2$		



1 Mounted on P.C. board with 3 mm² copper pad at each terminal
Montage auf Leiterplatte mit 3 mm² Kupferbelag (Löt-pad) an jedem Anschluss